

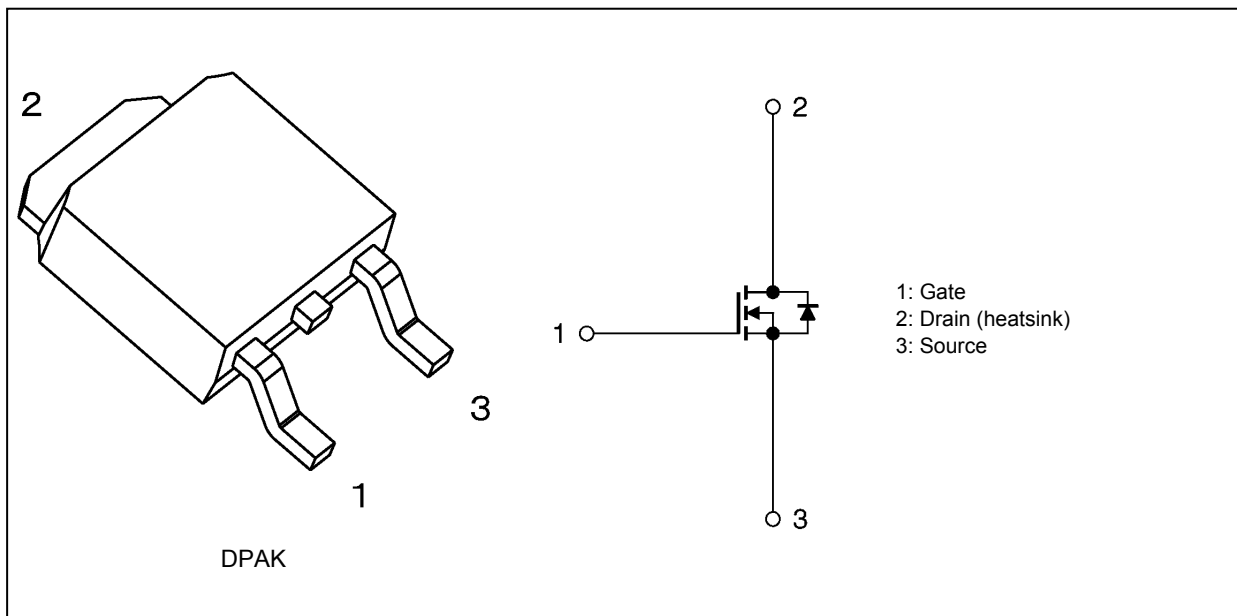
1. Applications

- Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 1.7 \Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (2) High forward transfer admittance: $|Y_{fs}| = 2.2 \text{ S}$ (typ.)
- (3) Low leakage current: $I_{DSS} = 10 \mu\text{A}$ (max) ($V_{DS} = 600 \text{ V}$)
- (4) Enhancement mode: $V_{th} = 2.4 \text{ to } 4.4 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Gate-source voltage	V_{GSS}	± 30	
Drain current (DC)	(Note 1) I_D	3.5	A
Drain current (pulsed)	(Note 1) I_{DP}	14	
Power dissipation	($T_c = 25^\circ\text{C}$) P_D	80	W
Single-pulse avalanche energy	(Note 2) E_{AS}	132	mJ
Avalanche current	I_{AR}	3.5	A
Repetitive avalanche energy	(Note 3) E_{AR}	8	mJ
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	1.56	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 18.9\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = 3.5\text{ A}$

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

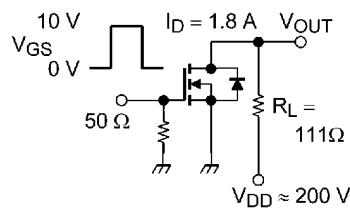
6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	600	—	—	V
Gate threshold voltage	V_{th}	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	2.4	—	4.4	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 1.8\text{ A}$	—	1.7	2.2	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 1.8\text{ A}$	0.6	2.2	—	S

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	490	—	μF
Reverse transfer capacitance	C_{rss}		—	3	—	
Output capacitance	C_{oss}		—	55	—	
Switching time (rise time)	t_r	See Figure 6.2.1	—	18	—	ns
Switching time (turn-on time)	t_{on}		—	40	—	
Switching time (fall time)	t_f		—	8	—	
Switching time (turn-off time)	t_{off}		—	55	—	



Duty $\leq 1\%$, $t_w = 10\ \mu\text{s}$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 3.5\text{ A}$	—	11	—	nC
Gate-source charge	Q_{gs}		—	6	—	
Gate-drain charge	Q_{gd}		—	5	—	

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 1)	I_{DR}	—	—	—	3.5	A
Reverse drain current (pulsed) (Note 1)	I_{DRP}	—	—	—	14	
Diode forward voltage	V_{DSF}	$I_{DR} = 3.5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 3.5\text{ A}, V_{GS} = 0\text{ V}$ $dI_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	1000	—	ns
Reverse recovery charge	Q_{rr}		—	5.0	—	μC

Note 1: Ensure that the channel temperature does not exceed 150°C .

7. Marking (Note)

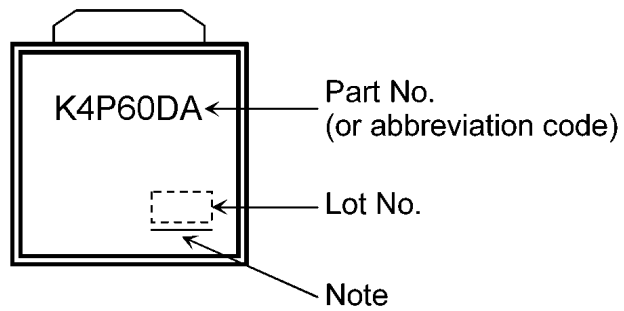


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

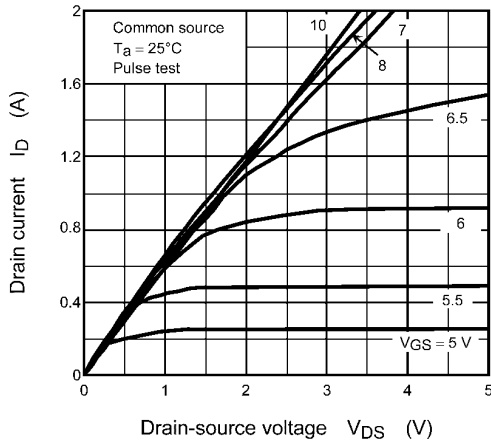


Fig. 8.1 $I_D - V_{DS}$

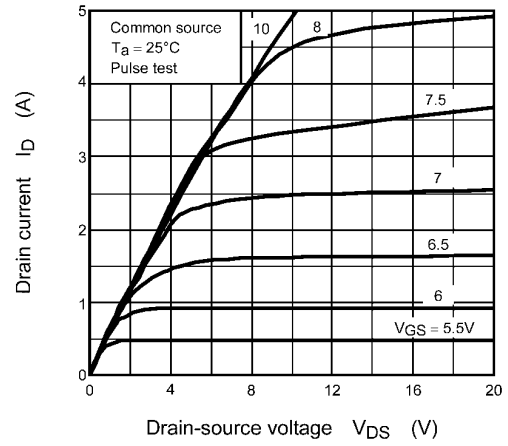


Fig. 8.2 $I_D - V_{DS}$

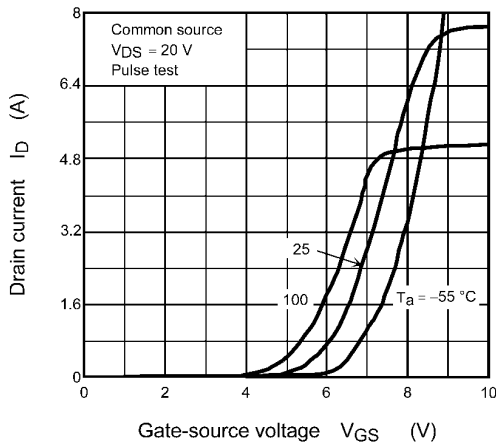


Fig. 8.3 $I_D - V_{GS}$

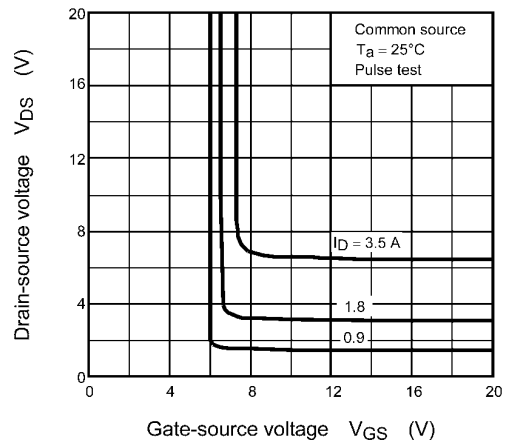


Fig. 8.4 $V_{DS} - V_{GS}$

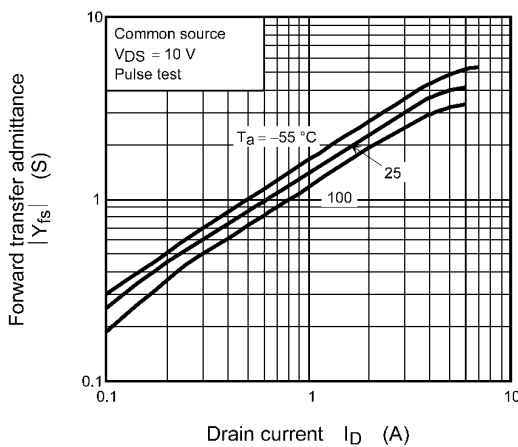


Fig. 8.5 $|Y_{fs}| - I_D$

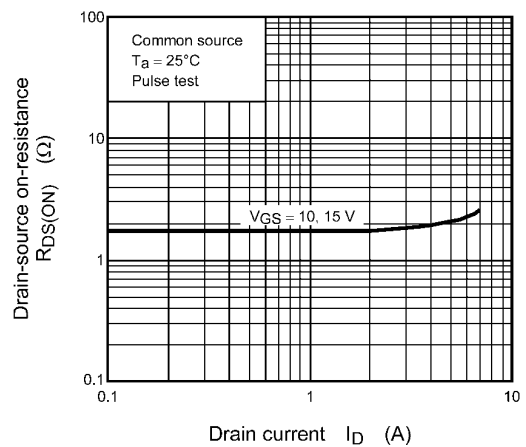


Fig. 8.6 $R_{DS(ON)} - I_D$

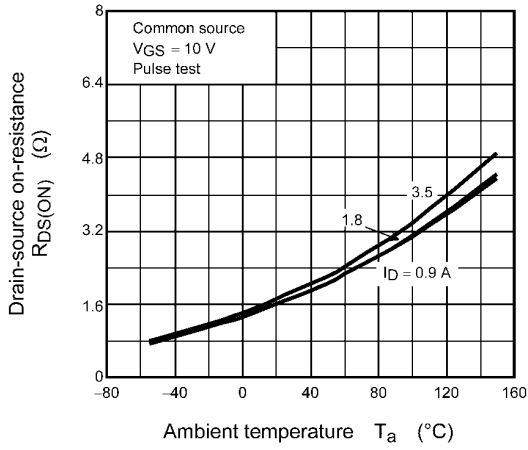


Fig. 8.7 $R_{DS(ON)} - T_a$

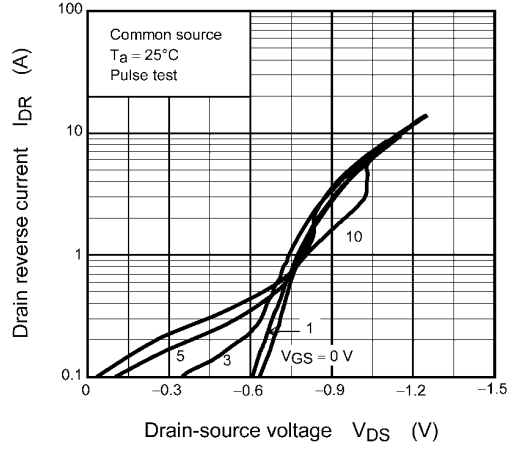


Fig. 8.8 $I_{DR} - V_{DS}$

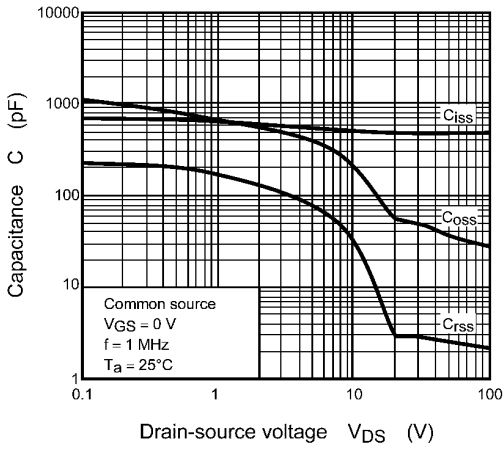


Fig. 8.9 Capacitance - V_{DS}

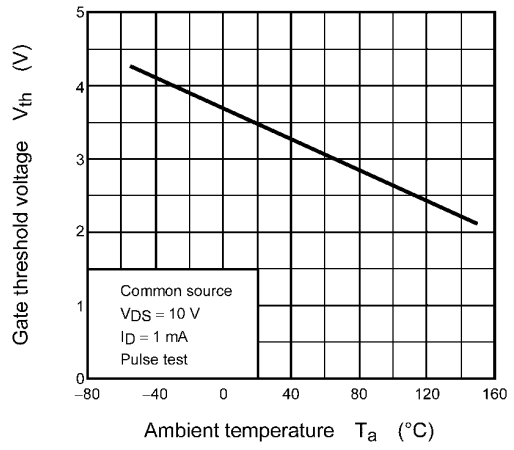
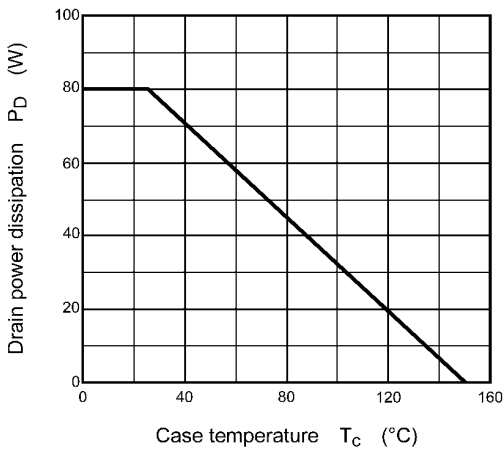


Fig. 8.10 $V_{th} - T_a$



**Fig. 8.11 $P_D - T_c$
(Guaranteed Maximum)**

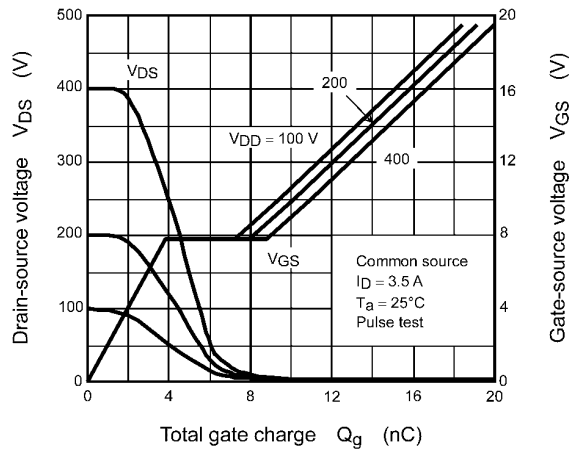


Fig. 8.12 Dynamic Input/Output Characteristics

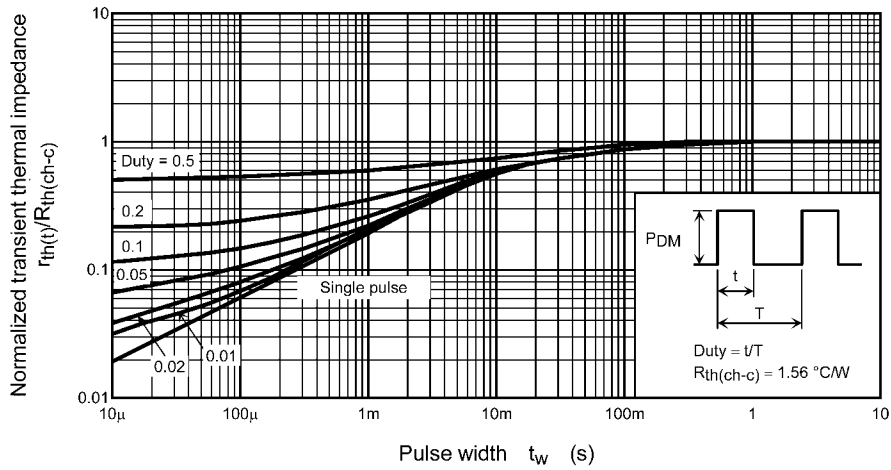


Fig. 8.13 $r_{th}(t)/R_{th}(ch-c) - t_w$
(Guaranteed Maximum)

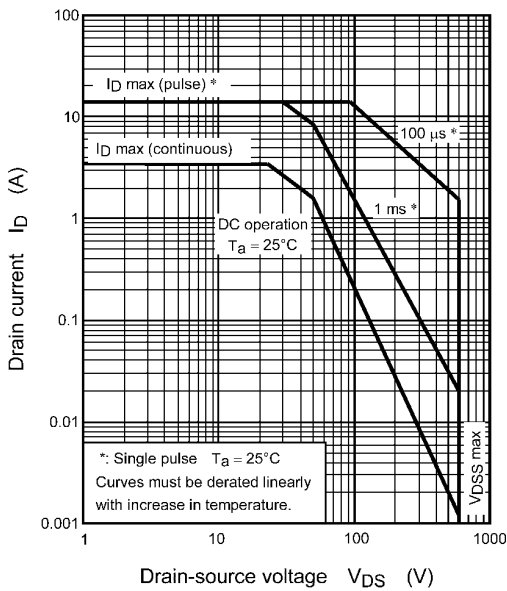


Fig. 8.14 Safe Operating Area
(Guaranteed Maximum)

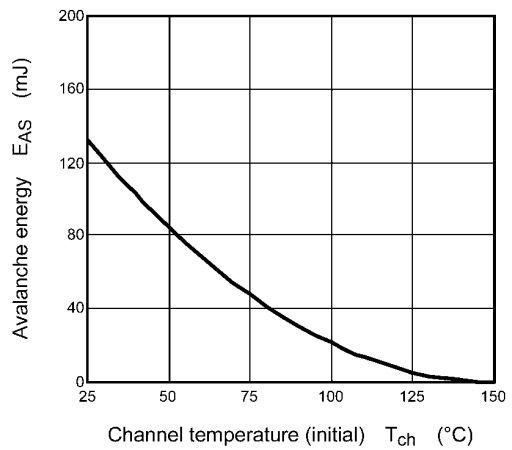
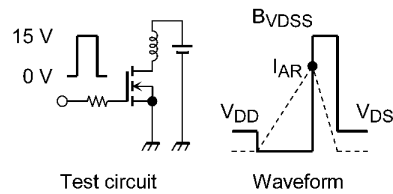


Fig. 8.15 $E_{AS} - T_{ch}$
(Guaranteed Maximum)

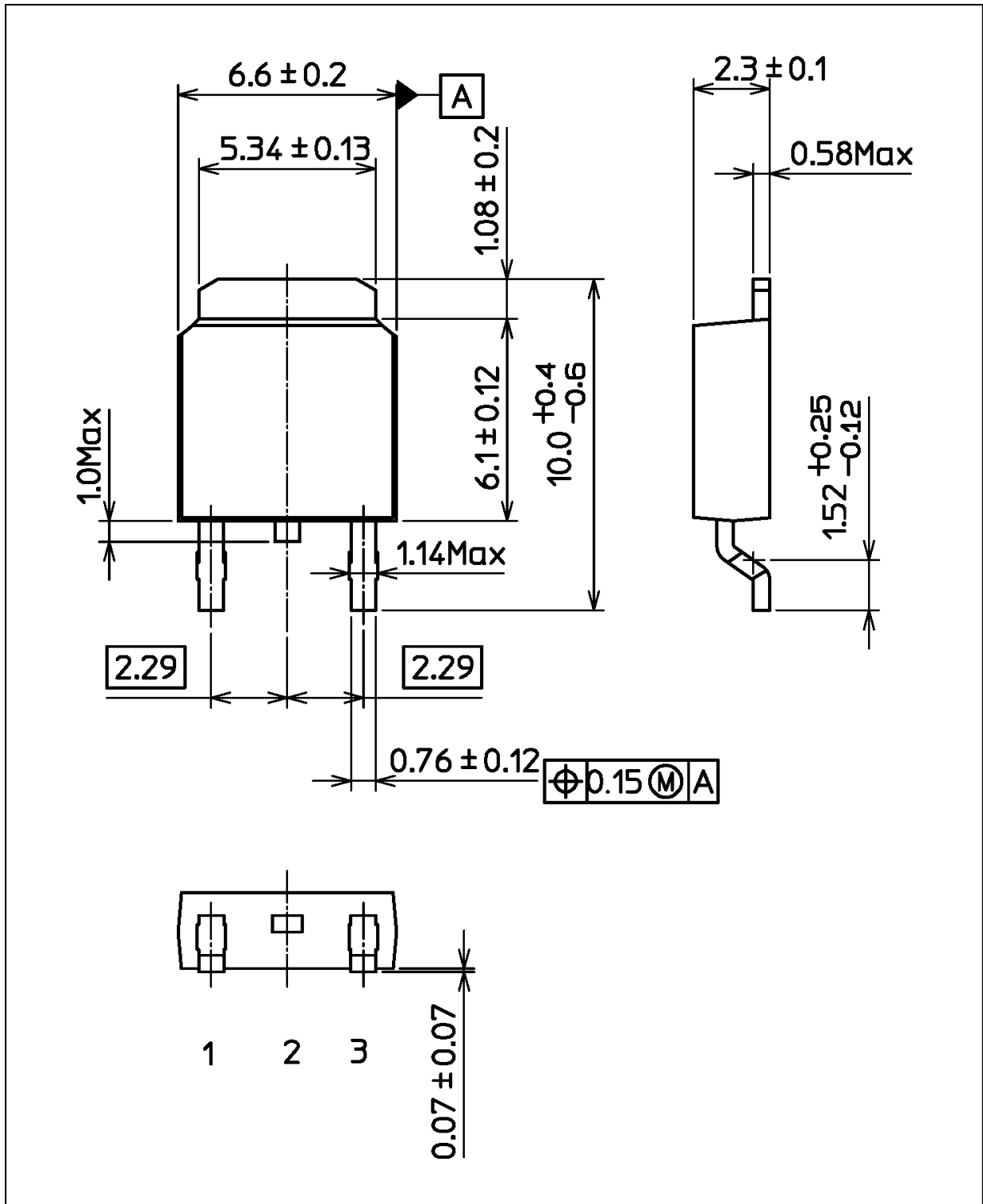


$$R_G = 25 \Omega \quad V_{DD} = 90 \text{ V}, L = 18.9 \text{ mH} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$

Fig. 8.16 Test Circuit/Waveform

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)